

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-12 (Canceled)

Claim 13 (Currently amended): An interconnect assembly comprising:

a ~~substrate~~ semiconductor wafer comprising a plurality of dies;
a plurality of resilient contact element elements attached to said dies, said contact elements on each die disposed to electrically connect said die to an electronic component; and
~~having at least a portion thereof which is capable of moving to a first position in which said resilient contact element is in mechanical and electrical contact with another contact element, said resilient contact element being disposed on said substrate;~~
a ~~stop structure~~ sheet material disposed on said substrate semiconductor wafer and comprising openings for said resilient contact elements, said sheet forming stop structures each defining a minimum separation between one of said dies and said electronic component said stop structure defining said first position;
~~wherein said another contact element is disposed on another substrate, and wherein said stop structure defines a separation between said substrate and said another substrate when said resilient contact element is in mechanical and electrical contact with said another contact element; and~~
~~wherein said stop structure is formed from a sheet material in which an opening exists and said resilient contact element is disposed in said opening.~~

Claim 14 (Canceled)

Claim 15 (Currently amended): An interconnect assembly as in ~~claim 14~~ claim 13 wherein said sheet material comprises an adhesive layer disposed to adhere one of said dies to said electronic component and a removable cover over said adhesive layer.

Claims 16-27 (Canceled)

Claim 28 (Currently amended): An interconnect assembly comprising:

a ~~first-substrate~~ semiconductor wafer comprising a plurality of dies;

a ~~first-contact element~~ plurality of contact elements disposed on said ~~first-substrate~~ dies of
said semiconductor wafer; and

a ~~stop-structure~~ sheet material disposed on said ~~first-substrate~~ semiconductor wafer and
comprising openings for said contact elements, said sheet forming stop structures each defining a
minimum separation between one of said dies and an electronic component comprising a
plurality of elongate, resilient contact elements disposed to electrically connect said electronic
component to said one of said dies.

~~;~~ ~~said stop-structure defining a first position of a resilient contact element in which said~~
~~resilient contact element is in mechanical and electrical contact with said first contact element;~~

~~wherein said resilient contact element is disposed on a second substrate and wherein said~~
~~resilient contact element has at least a portion thereof which is capable of moving to said first~~
~~position when said resilient contact element is compressed; and~~

~~wherein said stop-structure is formed from a sheet material in which an opening exists~~
~~and said first contact element is disposed in said opening.~~

Claim 29 (Canceled)

Claim 30 (Currently amended): An interconnect assembly as in ~~claim 29~~ claim 28 wherein said
sheet material comprises an adhesive layer disposed to adhere one of said dies to said electronic
component and a removable cover over said adhesive layer.

Claims 31 and 32 (Canceled)

Claim 33 (Currently amended): A method for forming ~~a stop structure on a substrate~~ stop structures on a plurality of semiconductor dies, said method comprising:

forming a plurality of openings in a sheet;

applying said sheet to ~~a substrate~~ an unsingulated semiconductor wafer comprising said dies; and

~~forming~~ disposing a plurality of resilient, elongate contact elements on said ~~substrate in locations corresponding to dies within~~ said plurality of openings, wherein said elongate contact elements on each die are disposed to electrically connect said die to an electronic component,

~~wherein said sheet comprises at least one region disposed around at least one of said openings which is said stop structure~~ said stop structures.

Claims 34-36

Claim 37 (Original): A method as in claim 33 wherein said sheet comprises a polyimide material.

Claim 38 (Currently amended): A method as in claim 33, wherein said sheet comprises an adhesive layer disposed to adhere one of said dies to said electronic component and a removable cover over said adhesive layer. ~~further comprising applying an adhesive layer to said sheet.~~

Claim 39 (Currently amended): A method as in claim 33 wherein said plurality of openings is formed before applying said sheet to said ~~substrate~~ semiconductor wafer and wherein said plurality of ~~contacts~~ resilient, elongate contact elements are formed before said sheet is applied to said ~~substrate~~ semiconductor wafer.

Claim 40 (Currently amended): A method as in claim 33 wherein said plurality of openings is formed after applying said sheet to said ~~substrate~~ semiconductor wafer.

Claims 41-50 (Canceled)

Claim 51 (Currently amended): A method for forming ~~a stop structure on a substrate~~ stop structures on a plurality of semiconductor dies, said method comprising:

applying a sheet to ~~said substrate~~ an unsingulated semiconductor wafer comprising said dies;

forming a plurality of openings in said sheet; and

forming at least one first contact element on said substrate a plurality of first contact elements on said dies within said openings, said first contact ~~element~~ elements having a first height relative to said ~~substrate~~ dies and said sheet having a second height relative to said ~~substrate~~ dies, said sheet ~~defining~~ comprising said stop structures each of which defines a minimum separation ~~which is capable of existing between said substrate~~ between one of said dies and ~~[[an]]~~ another substrate having ~~[[a]]~~ second contact ~~element~~ elements which ~~is~~ are in mechanical and electrical contact with said first contact elements on said one of said dies ~~said first contact element when said minimum separation exists.~~

Claim 52 (Currently amended): A method as in claim 51 wherein said sheet ~~is a perimeter stop structure~~ comprises a plurality of perimeter stop structures.

Claim 53 (Currently amended): A method as in claim 51 wherein said first contact ~~element is a resilient contact element~~ elements are resilient and said first height is greater than said second height.

Claim 54 (Currently amended): A method as in claim 51 wherein said second contact ~~element is a resilient contact element~~ elements are resilient and said first height is less than said second height.

Claim 55 (Currently amended): A method as in claim 51 wherein said sheet comprises an adhesive material which secures said sheet to said ~~substrate~~ semiconductor wafer.

Claim 56 (Currently amended): A method as in claim 51 wherein said sheet covers only a portion of said ~~substrate~~ semiconductor wafer.

Claim 57 (Canceled)

Claim 58 (New): The interconnect assembly of claim 13, wherein said sheet material comprises patterned photoresist.

Claim 59 (New): The interconnect assembly of claim 13, wherein said sheet material hermetically seals said dies.

Claim 60 (New): The interconnect assembly of claim 13, wherein said sheet material comprises a polyimide material.

Claim 61 (New): The interconnect assembly of claim 13, wherein said sheet material comprises:
a plurality of perimeter structures, each said perimeter structure disposed about a
perimeter of one of said dies and comprising one of said openings, and
a web structure interconnecting said plurality of perimeter structures.

Claim 62 (New): The interconnect assembly of claim 28, wherein said sheet material comprises patterned photoresist.

Claim 63 (New): The interconnect assembly of claim 28, wherein said sheet material hermetically seals said dies.

Claim 64 (New): The interconnect assembly of claim 28, wherein said sheet material comprises a polyimide material.

Claim 65 (New): The interconnect assembly of claim 28, wherein said sheet material comprises:
a plurality of perimeter structures, each said perimeter structure disposed about a
perimeter of one of said dies and comprising one of said openings, and
a web structure interconnecting said plurality of perimeter structures.

Claim 66 (New): The method of claim 33, wherein said step of applying said sheet comprises forming said sheet on said wafer.

Claim 67 (New): The method of claim 66, wherein said step of forming said sheet comprises depositing photoresist over said semiconductor wafer.

Claim 68 (New): The method of claim 67, wherein said step of forming a plurality of openings comprises lithographically patterning said openings in said photoresist.

Claim 69 (New): The method of claim 33, wherein said sheet comprises an epoxy material.

Claim 70 (New): The method of claim 33, wherein said sheet hermetically seals said dies.

Claim 71 (New): The method of claim 33, wherein said sheet comprises:

a plurality of perimeter structures, each said perimeter structure disposed about a perimeter of one of said dies, each said perimeter structure comprising one of said openings, a web structure interconnecting said plurality of perimeter structures.

Claim 72 (New): The method of claim 71 further comprising singulating said dies from said wafer.

Claim 73 (New): The method of claim 72, wherein said singulating step comprises severing said web structure between perimeter structures.

Claim 74 (New): The method of claim 38 further comprising singulating said dies from said wafer.

Claim 75 (New): The method of claim 74 further comprising:

removing said cover from said adhesive layer on one of said singulated dies, and adhering said singulated die to said electronic component.

Claim 76 (New): The method of claim 33, wherein said disposing step comprises forming said contact elements on said dies within said openings